

InGaAs 1100-1654nm PD Devices

P/N:YBPD-RA-70BR-BG(S)

❖ Features

- High responsivity
- Low dark current, Low capacitance
- Laser Welding, High reliability And Long operation life
- InGaAs PIN-PD as Receiver

❖ Absolute Maximum Ratings (Tc=25C)

Parameter	Symbol	Min.	Type	Max.	Unit
Saturation power	Ps	3	-	-	dBm
Forward Current	If	-	-	10	mA
Reverse Voltage	Vr	-	5	15	V
Operating Case Temperature	Top	--40	-	+85	°C
Storage Temperature	Tstg	--40	-	+85	°C
Lead Soldering(Temperature/Time)	-	-	260/10 or 360/5	-	°C/Sec

❖ Optical and Electrical Characteristics (Tc=25C)

Parameter	Symbol	Min.	Type	Max.	Unit	Test condition
Active Area	ϕ	-	70	-	μm	
Operating Wavelength	λ	1100	-	1650	nm	
Responsivity	R	0.85	0.90	-	A/W	Vr=5V, λ =1310nm
Dark Current	Id	-	-	1	nA	Vr=5V
Capacitance	C	-	-	0.75	pF	Vr=5V,f=1MHz,case open
Rise time/Fall time	Tr/Tf	-	-	0.5	ns	Vr=5V,10~90%
Bandwidth	Bw	1.25	-	-	GHz	Vr=5V,50 Ω load with lead length=6mm,case open

❖ Outline Diagram and Pin Assignments

